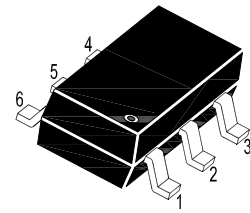
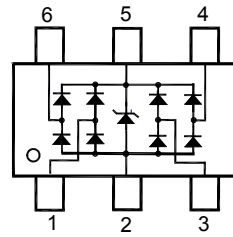


ESDULC6-4D

4-Channel ESD Protection Diode

Features

- Low clamping voltage
- Low capacitance



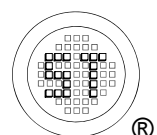
1. I/O1 2. GND 3. I/O2
4. I/O3 5. V_{BUS} 6. I/O4
SOT-26 Plastic Package

Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit
Peak Pulse Power (tp = 8/20 μs)	P _{PK}	85	W
Peak Pulse Current (tp = 8/20 μs)	I _{PP}	5	A
IEC61000-4-2 (ESD) Air Contact	V _{ESD}	±15 ±15	KV
Maximum Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55 to + 150	°C

Characteristics at T_a = 25°C

Parameter	Symbol	Min.	Max.	Unit
Reverse Stand-Off Voltage	V _{RWM}	-	5	V
Reverse Breakdown Voltage at I _R = 1 mA, Pin 5 to Pin 2	V _{(BR)R}	6	11	V
Leakage Current at V _R = 5 V	I _R	-	0.5	μA
Forward Voltage at I _F = 10 mA, Pin 2 to Pin 5	V _F	-	1.2	V
Clamping Voltage at I _{PP} = 1 A, tp = 8/20 μs, Any I/O Pin to Pin 2	V _C	-	12	V
Clamping Voltage at I _{PP} = 5 A, tp = 8/20 μs, Any I/O Pin to Pin 2	V _C	-	17	V
Capacitance at V _R = 0 V, f = 1 MHz, Between I/O Pin to Pin 2	C _{i/o-GND}	-	1	pF
Capacitance at V _R = 0 V, f = 1 MHz, Between I/O Pins	C _{i/o-i/o}	-	0.5	pF



ESDULC6-4D

Electrical Characteristic Curves

Fig 1. Pulse Waveform

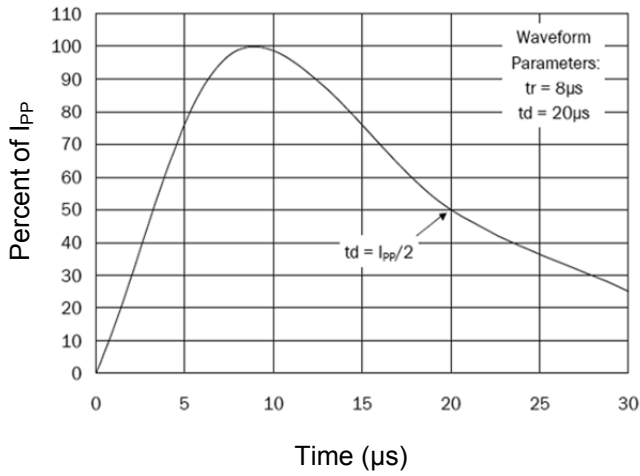


Fig 2. Power Derating Curve

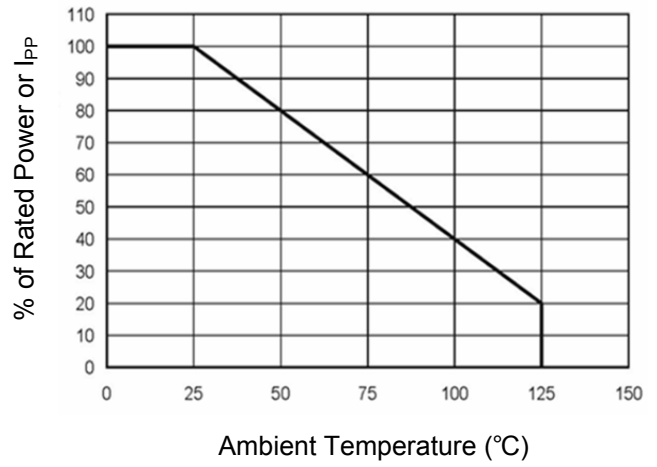


Fig 3. Clamping Voltage Curve

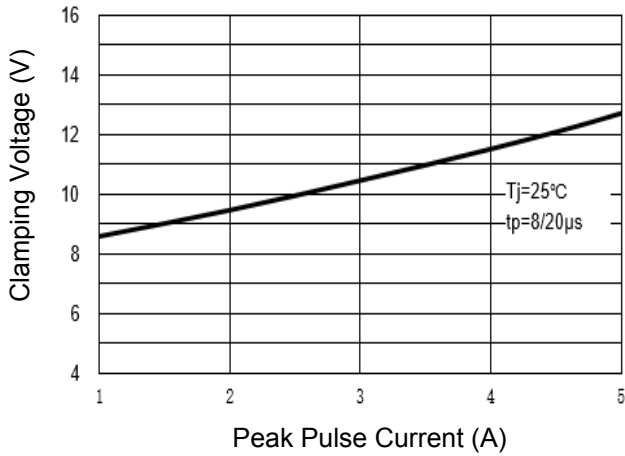


Fig 4. Junction Capacitance

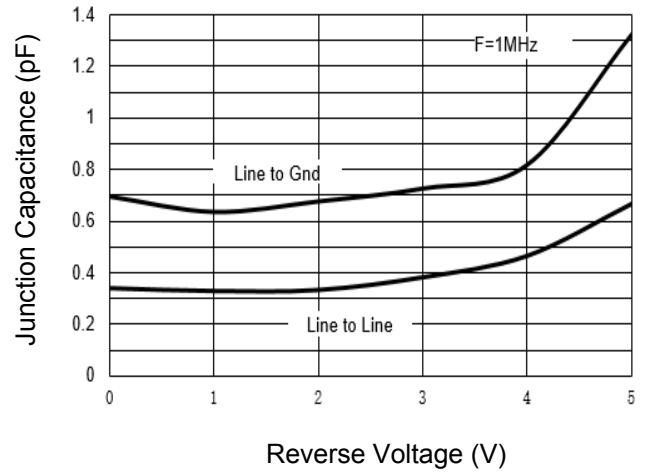
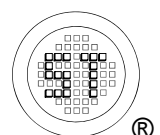
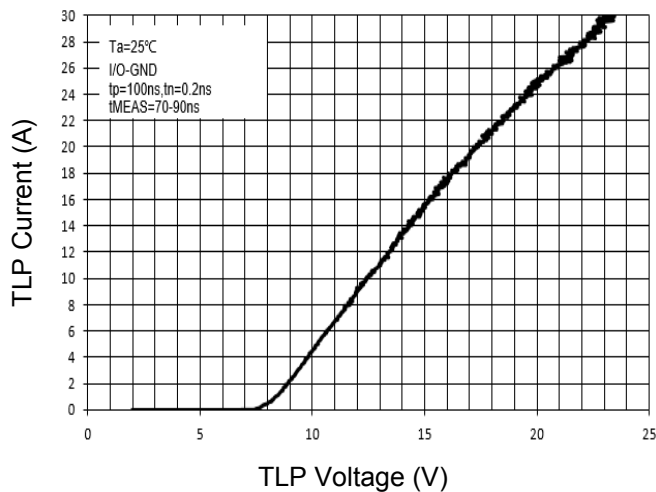


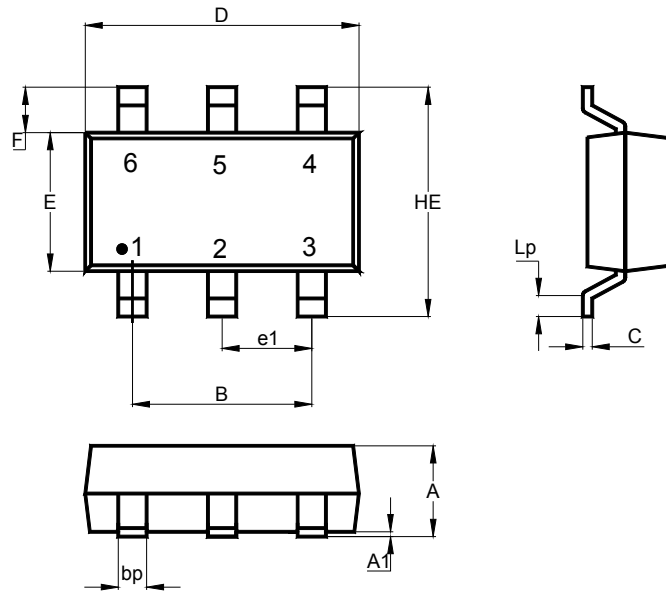
Fig 5 TLP Curve



ESDULC6-4D

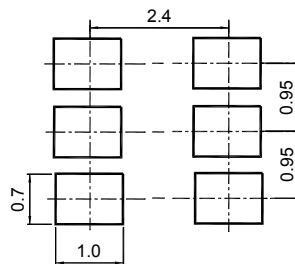
Package Outline (Dimensions in mm)

SOT-26



Unit	A	A1	B	C	D	E	e1	F	HE	Lp	bp
mm	1.2	0.1	2.1	0.20	3.1	1.7	0.95	0.65	3.0	0.6	0.5
	1.0	0	1.7	0.08	2.7	1.3	typ.	0.6	2.6	0.2	0.3

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-26	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

Marking information

"DL46" = Part No.
 "YM" = Date Code Marking
 "Y" = Year
 "M" = Month
 Font type: Arial

